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INFORMATION DISCLOSURE CITATION PTO-1449	Atty. Docket No. NMTI 1002-9	Serial No. 10/068,513-3666
	Applicant PIERRAT, Christophe	
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SRM	WO 01/23961 A1	4/5/2001	WO			☐	☐
SRM	JP 1,283,925	2/14/1991	JP			☒	☐
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SRM	JP 2-140743	5/30/1990	JP			☒	☐
SRM	GB 2,333,613 A	7/28/1999	GB			☐	☐
SRM	JP 2,638,561	4/25/1997	JP			☐	☐
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SRM	JP 8,051,068	2/20/1996	JP			☒	☐
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